

Title (en)

Semiconductor memory device with reduced leakage current and improved data retention

Title (de)

Halbleiterspeicheranordnung mit niedrigem Leckstrom und verbessertem Datenschutz

Title (fr)

Dispositif de mémoire à semi-conducteurs ayant un courant de fuite réduit et une sauvegarde de données améliorée

Publication

EP 0773550 A3 19990519 (EN)

Application

EP 96116986 A 19961022

Priority

JP 28879095 A 19951107

Abstract (en)

[origin: EP0773550A2] A semiconductor memory device has memory cells in which data are represented by a first voltage level and a second voltage level higher than the first voltage level. The memory cells are selected by word lines. When memory cells are not selected, the word lines are driven to a third voltage level lower than the first voltage level. <IMAGE>

IPC 1-7

G11C 8/00

IPC 8 full level

G11C 11/407 (2006.01); **G11C 8/08** (2006.01)

CPC (source: EP US)

G11C 8/08 (2013.01 - EP US)

Citation (search report)

- [XA] US 4628486 A 19861209 - SAKUI KOJI [JP]
- [XA] US 5416747 A 19950516 - OHIRA TSUYOSHI [JP]
- [A] EP 0559995 A1 19930915 - ST MICROELECTRONICS SRL [IT]

Cited by

US7706209B2; US5936892A; DE19738642A1; US5920517A; US5930185A; US5923601A; WO9814956A1

Designated contracting state (EPC)

DE FR NL

DOCDB simple family (publication)

EP 0773550 A2 19970514; EP 0773550 A3 19990519; EP 0773550 B1 20020123; DE 69618747 D1 20020314; DE 69618747 T2 20040506; JP H09134591 A 19970520; KR 100327780 B1 20020821; TW 332333 B 19980521; US 5781481 A 19980714

DOCDB simple family (application)

EP 96116986 A 19961022; DE 69618747 T 19961022; JP 28879095 A 19951107; KR 19960052341 A 19961106; TW 85113233 A 19961030; US 74218196 A 19961030